

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

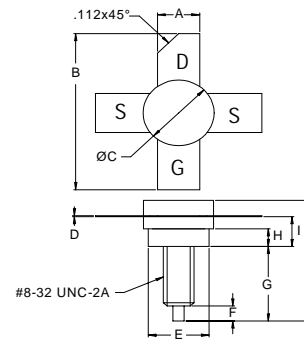
The **ASI TVV010** is Designed for Television Band III Applications up to 225 MHz.

**FEATURES:**

- Common Emitter
- $P_G = 10$  dB at 10 W/225 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	10 A
$V_{CB}$	60 V
$V_{CE}$	35 V
$P_{DISS}$	140 W @ $T_C = 25^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
$\theta_{JC}$	$2.2^\circ\text{C/W}$

**PACKAGE STYLE .380 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

**ORDER CODE: ASI10656**
**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA	35			V
$BV_{CER}$	$I_C = 50$ mA $R_{BE} = 10 \Omega$	60			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CES}$	$V_E = 28$ V			5	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		100	---
$P_{GE}$	$V_{CE} = 25$ V $I_C = 1.6$ A $f = 225$ MHz	10			dB
$IMD_1$	$P_{OUT} = 10$ W	-54			dBc